

Silicon NPN Power Transistors

2SC3962

DESCRIPTION

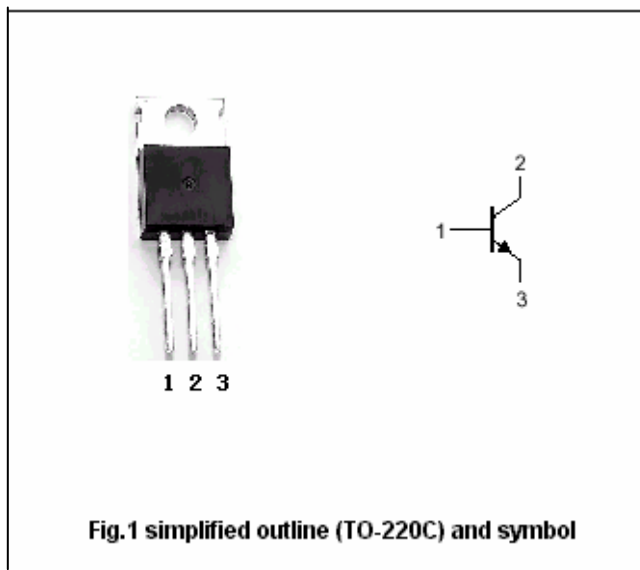
- With TO-220C package
- High voltage
- High speed switching

APPLICATIONS

- For switching regulator and general purpose applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	500	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	400	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		5	A
I <sub>CM</sub>	Collector current-peak		10	A
I <sub>B</sub>	Base current		2	A
P <sub>C</sub>	Collector dissipation	T <sub>C</sub> =25°C	40	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=25mA ; I_B=0$	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	7			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=2A ; I_B=0.4A$			0.5	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C=2A ; I_B=0.4A$			1.3	V
$I_{CBO}$	Collector cut-off current	$V_{CB}=500V ; I_E=0$			100	$\mu A$
$I_{EBO}$	Emitter cut-off current	$V_{EB}=7V ; I_C=0$			100	$\mu A$
$h_{FE}$	DC current gain	$I_C=0.5A ; V_{CE}=5V$	15		50	

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PACKAGE OUTLINE

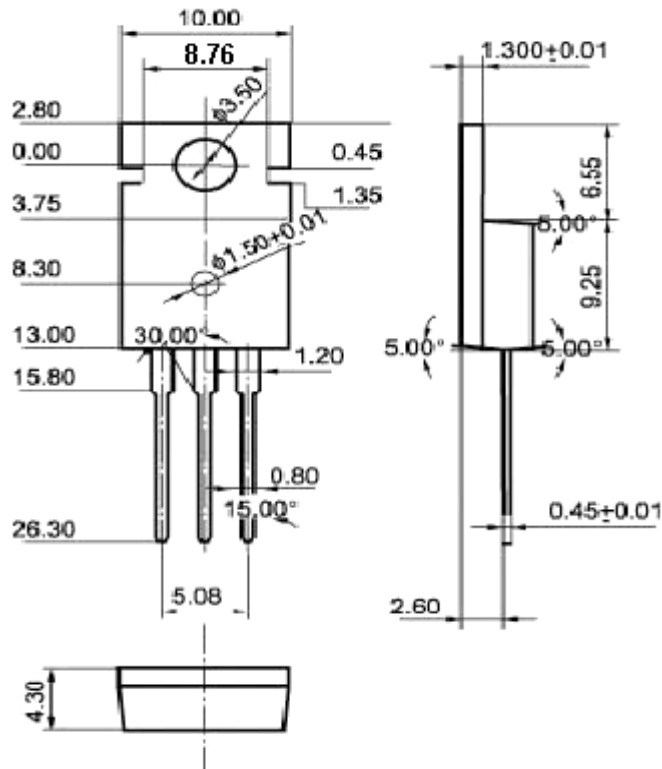


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)